

Title: SI-MOS HIGH-FREQUENCY SEMICONDUCTOR DEVICE AND THE MANUFACTURING METHOD

OF THE SAME

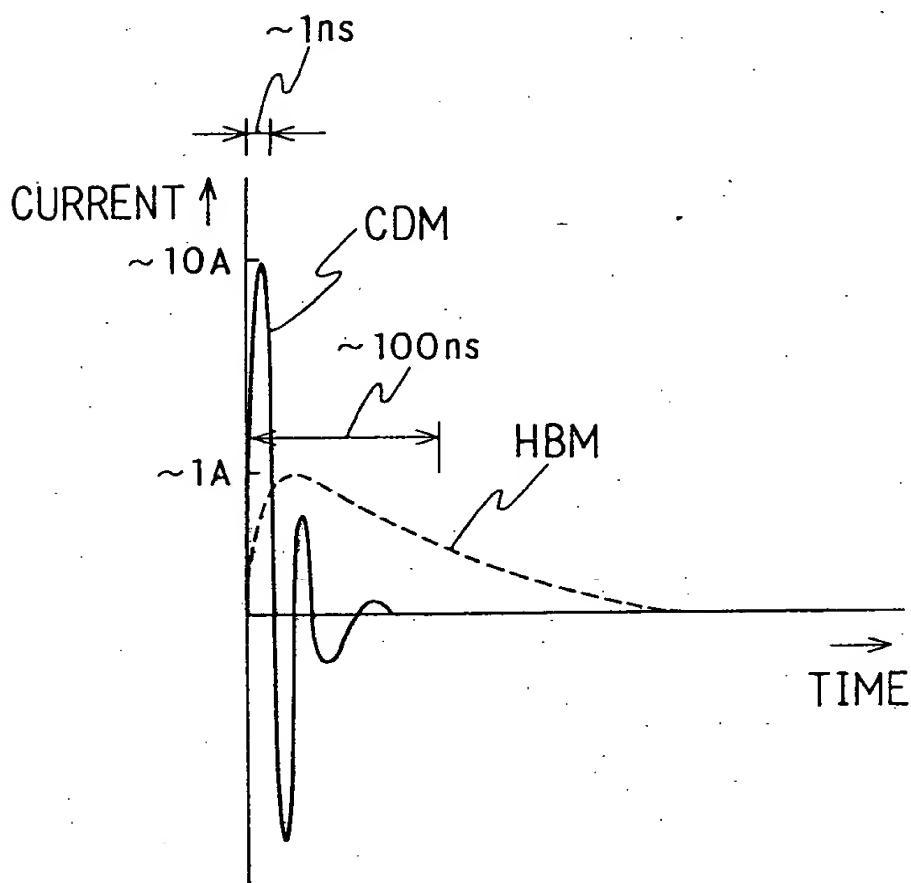
Inventors: Takahiro OHNAKADO

Atty Docket No.: 401308

Leydig, Voit & Mayer, Ltd.

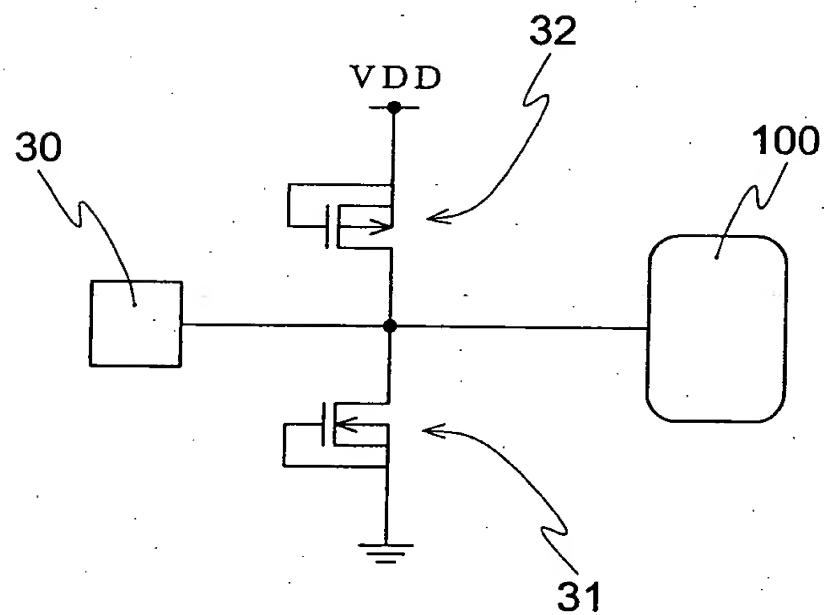
202-737-6770

F I G . 1



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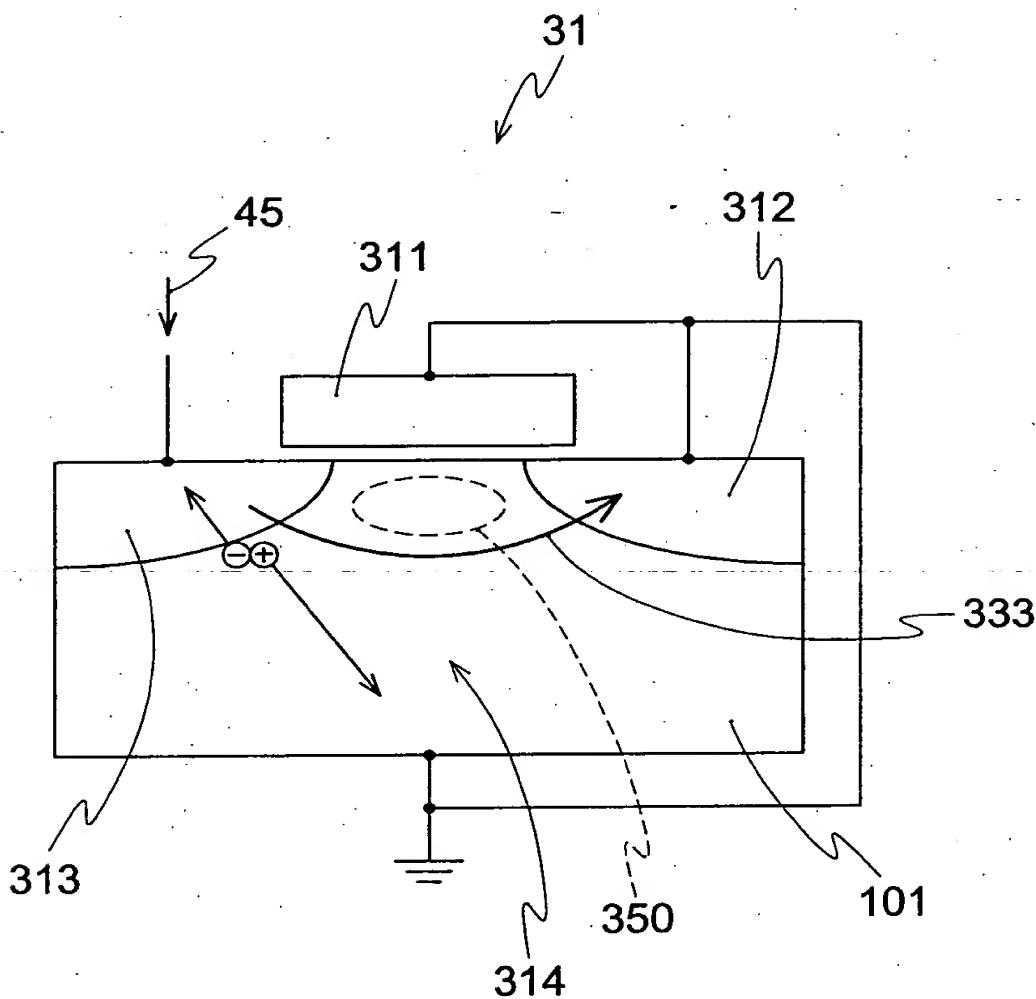
FIG. 2



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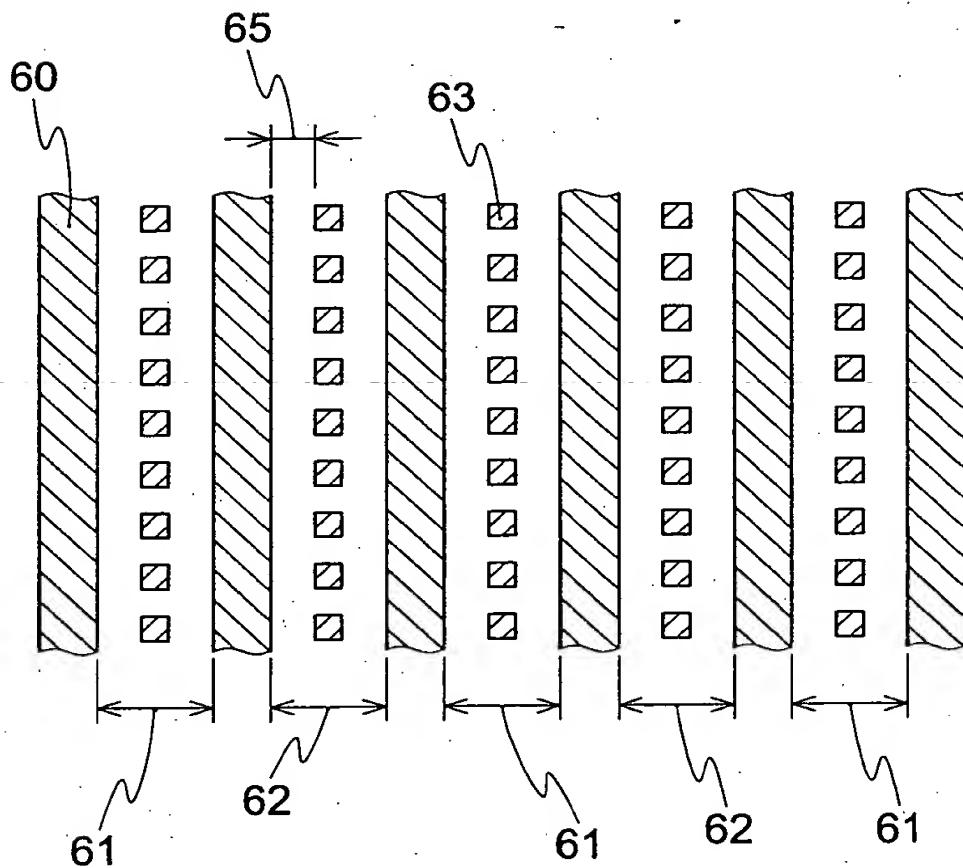
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FIG. 3



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FIG. 4



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FIG. 5

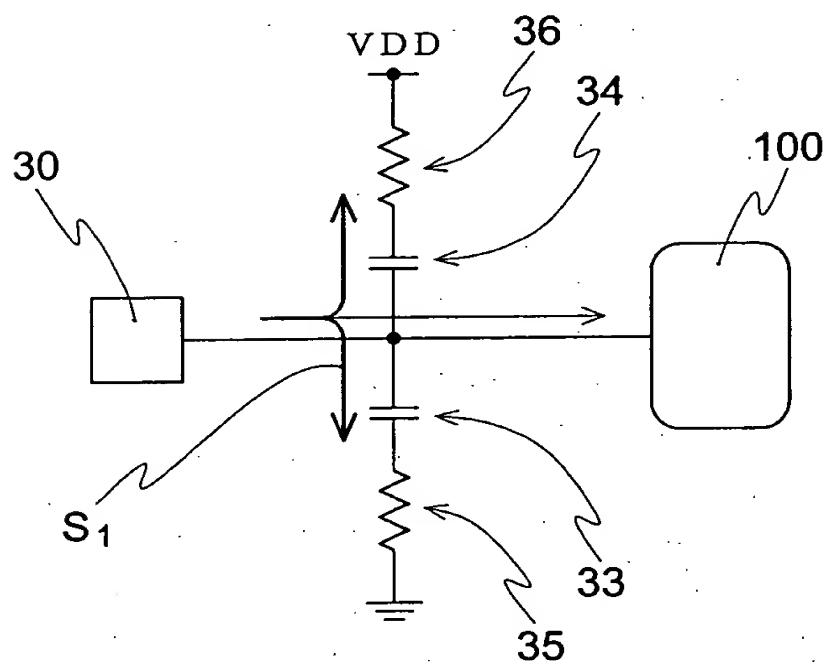


FIG. 6(a)

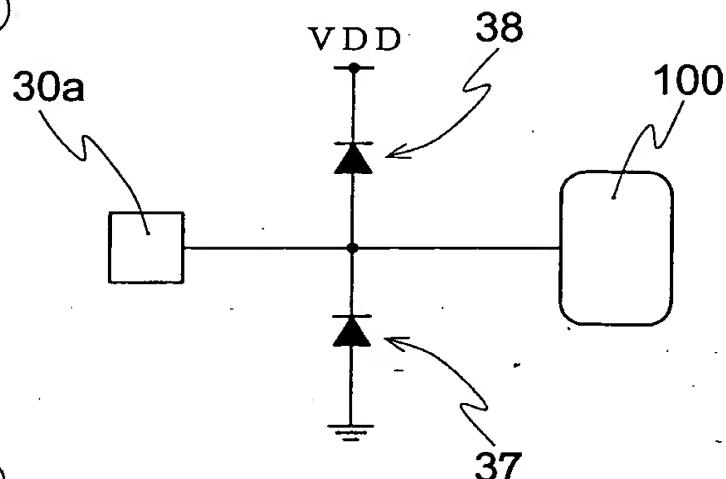


FIG. 6(b)

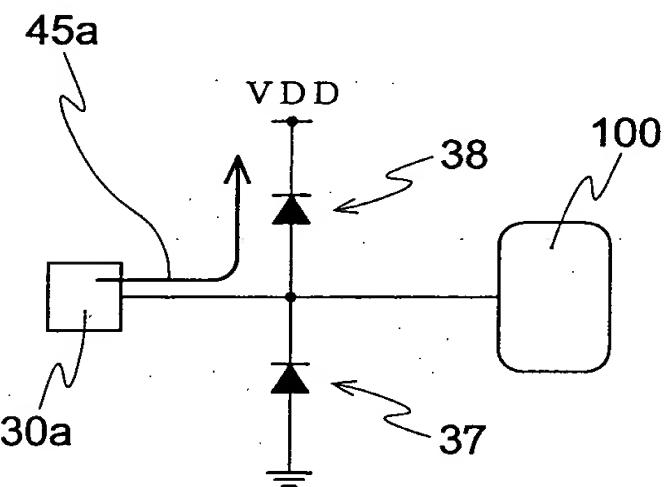
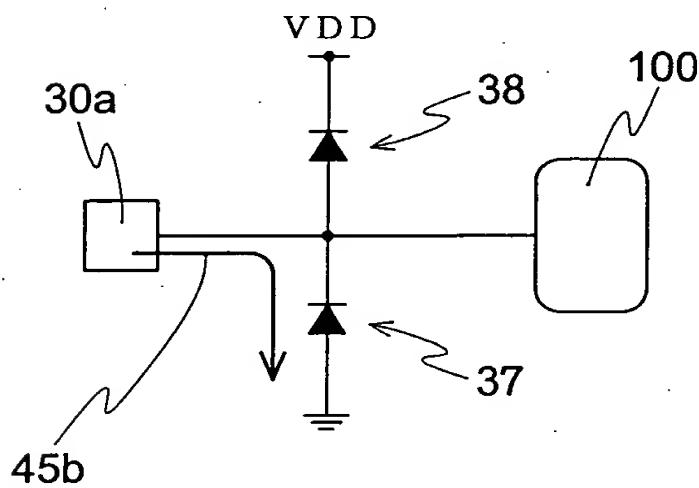


FIG. 6(c)



Title: SI-MOS HIGH-FREQUENCY SEMICONDUCTOR DEVICE AND THE MANUFACTURING METHOD
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FIG. 7(a)

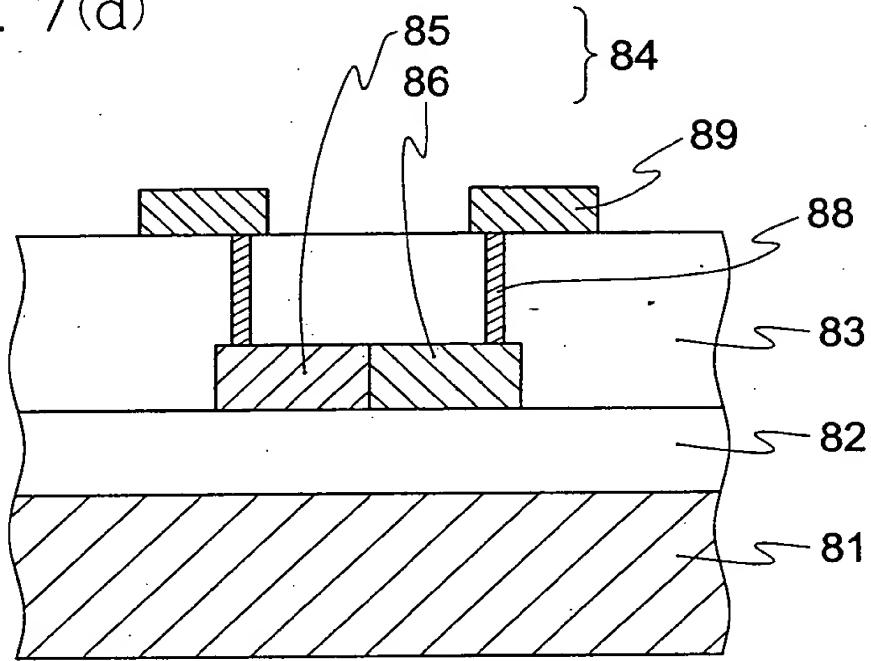
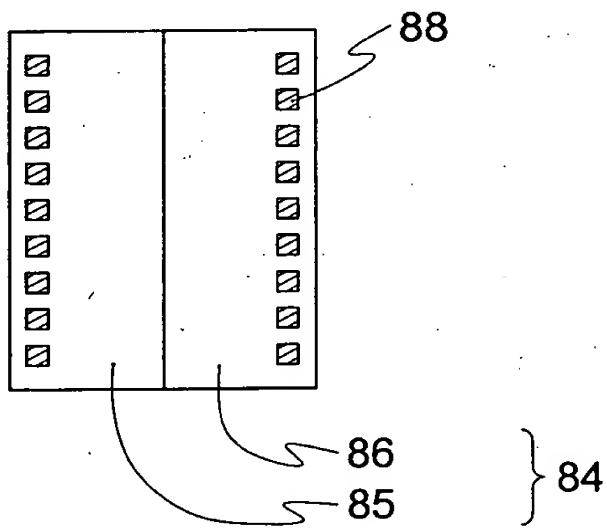


FIG. 7(b)



Title: SI-MOS HIGH-FREQUENCY SEMICONDUCTOR DEVICE AND THE MANUFACTURING METHOD
OF THE SAME

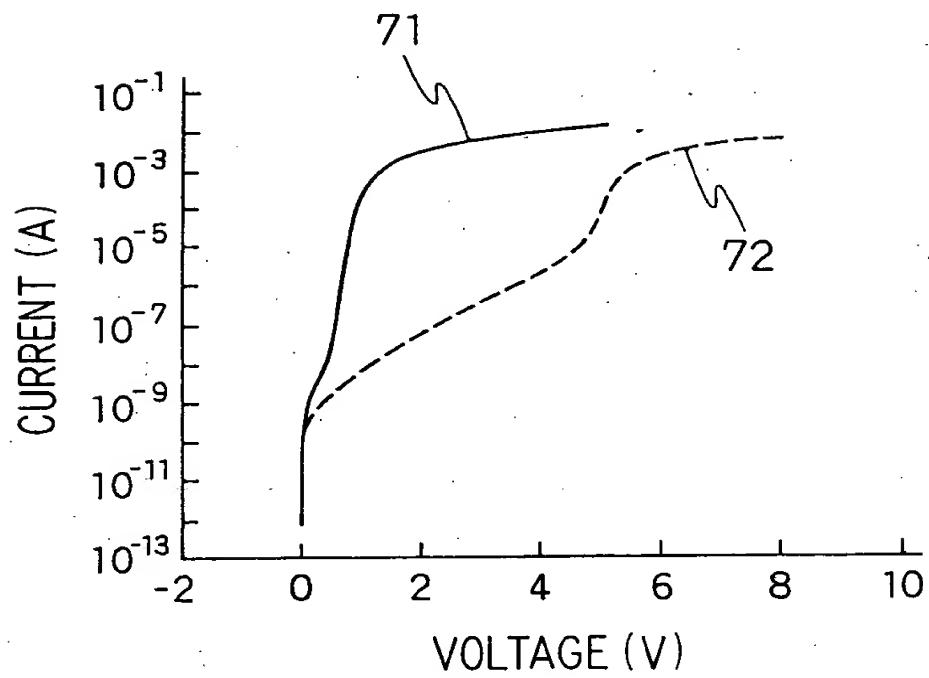
Inventors: Takahiro OHNAKADO

Atty Docket No.: 401308

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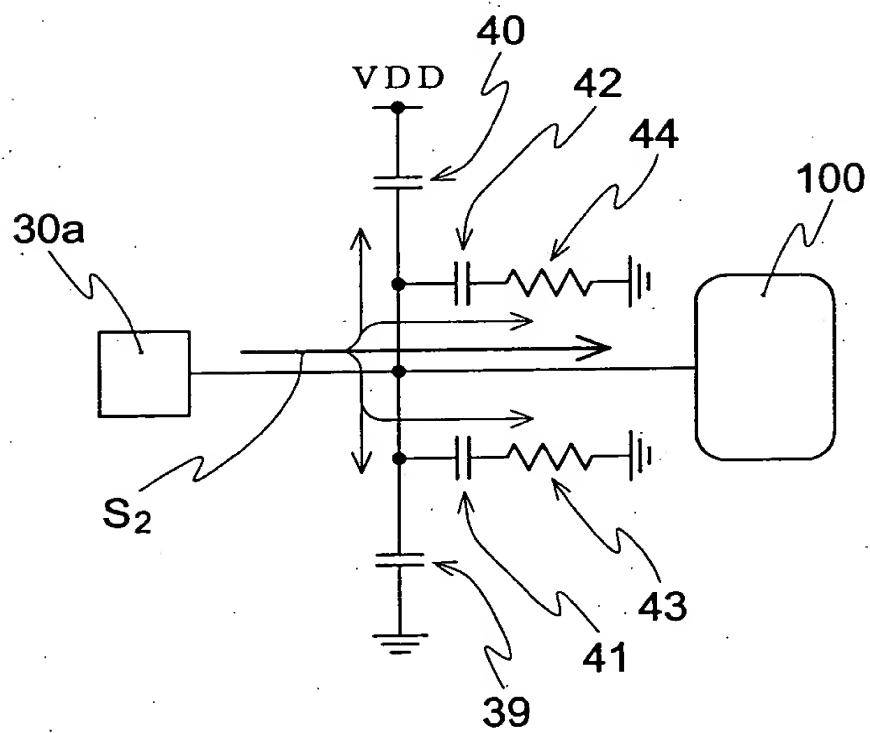
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FIG. 8



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FIG. 9



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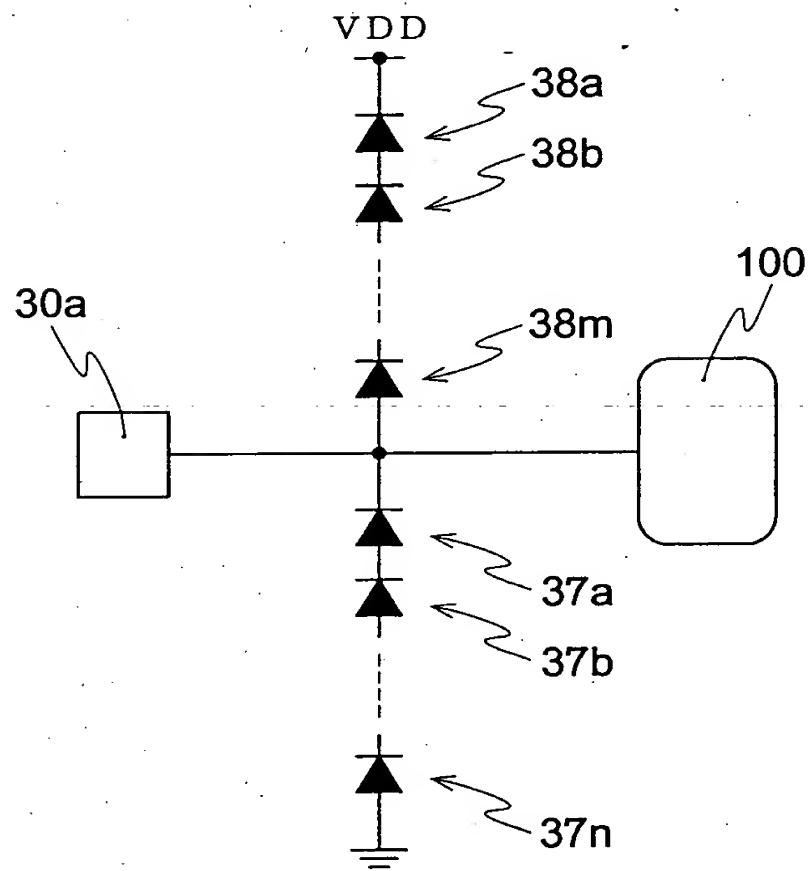
Inventors: Takahiro OHNAKADO

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FIG.10



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FIG. 11(a)

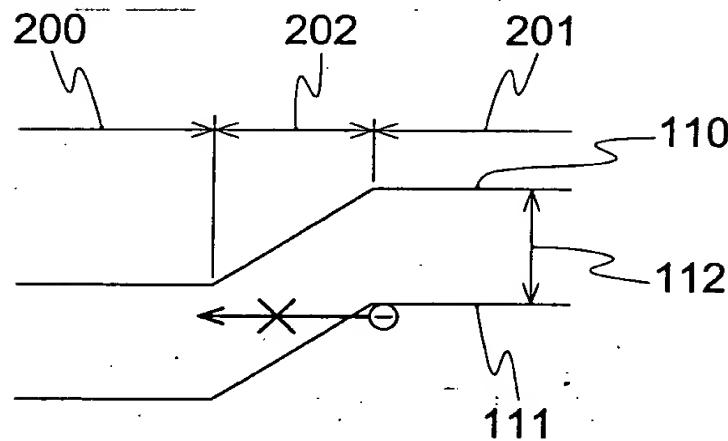


FIG. 11(b)

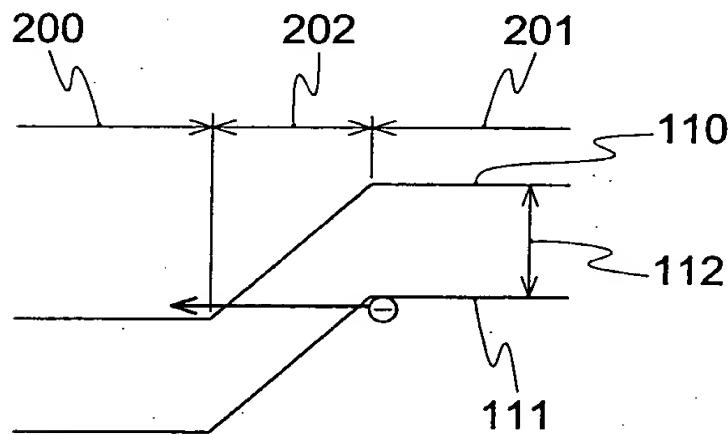
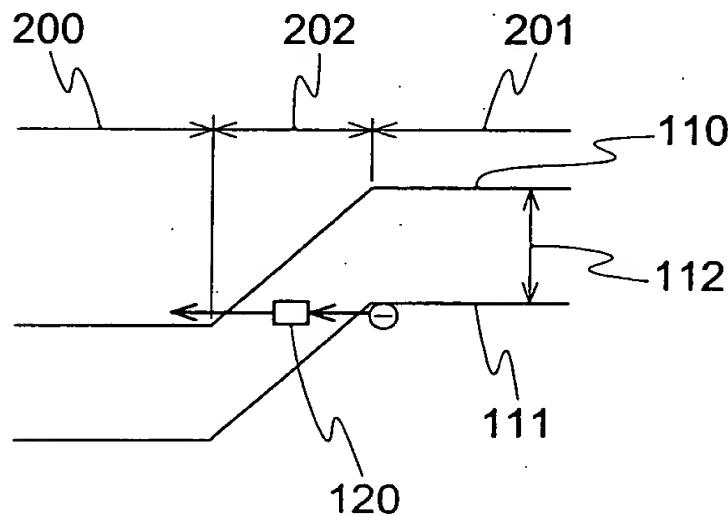


FIG. 11(c)



Title: SI-MOS HIGH-FREQUENCY SEMICONDUCTOR DEVICE AND THE MANUFACTURING METHOD
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FIG. 12(a)

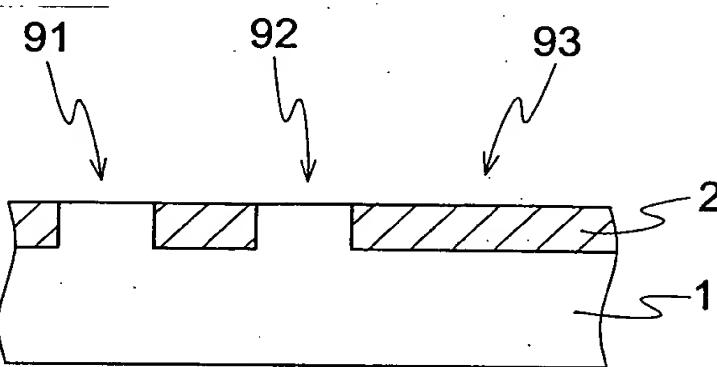


FIG. 12(b)

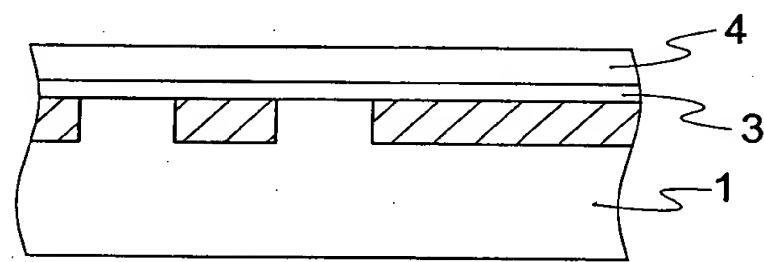
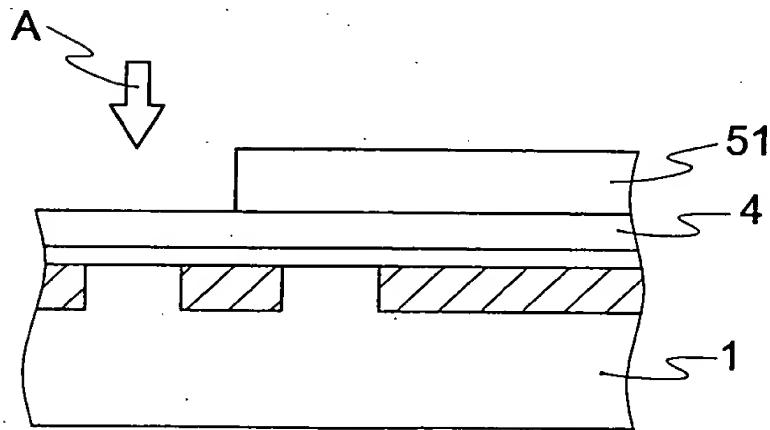


FIG. 12(c)



Title: SI-MOS HIGH-FREQUENCY SEMICONDUCTOR DEVICE AND THE MANUFACTURING METHOD
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FIG. 13 (a)

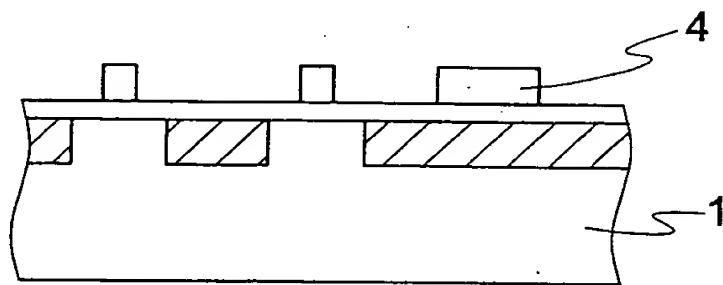


FIG. 13 (b)

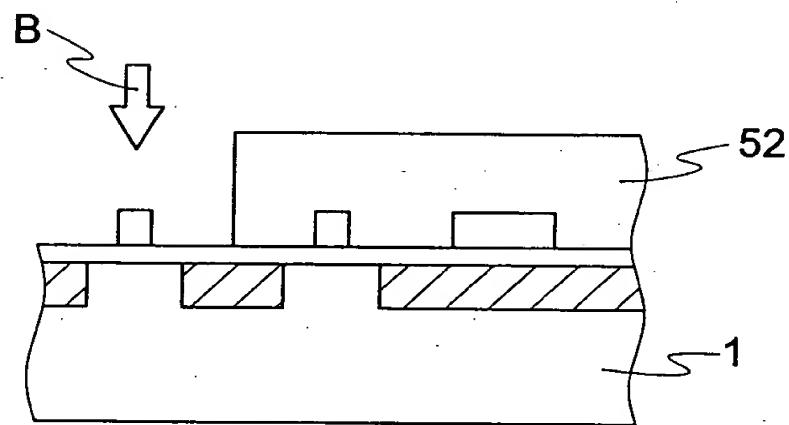
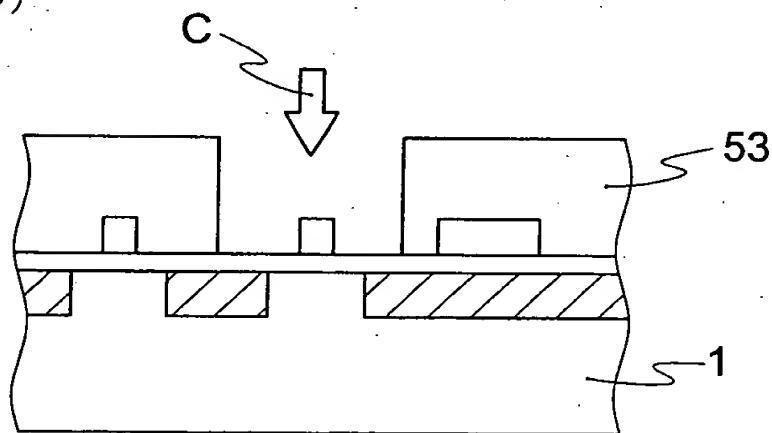


FIG. 13 (c)



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FIG. 14 (a)

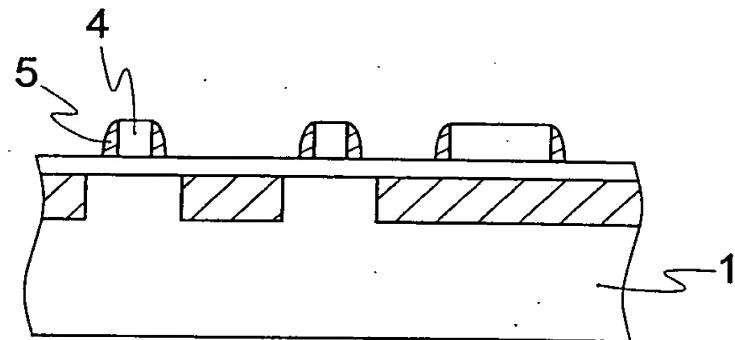


FIG. 14 (b)

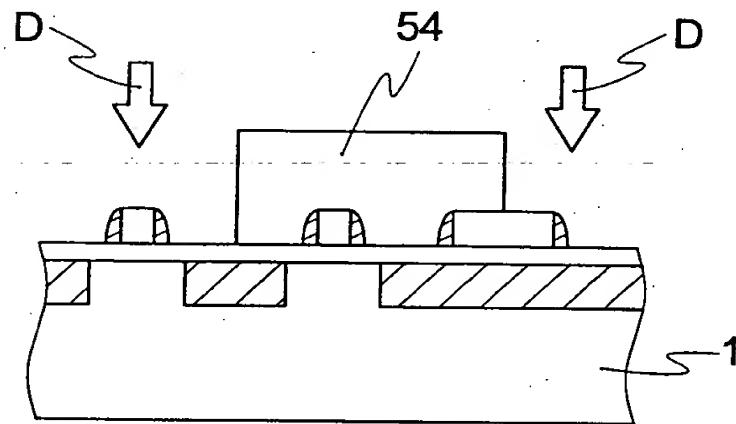
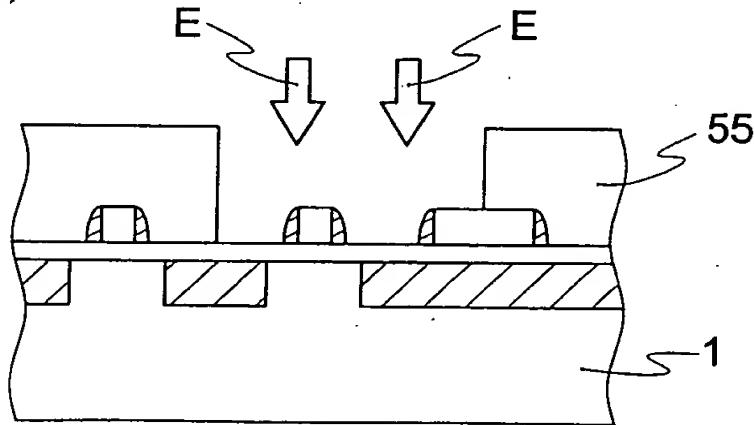


FIG. 14 (c)



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FIG. 15 (a)

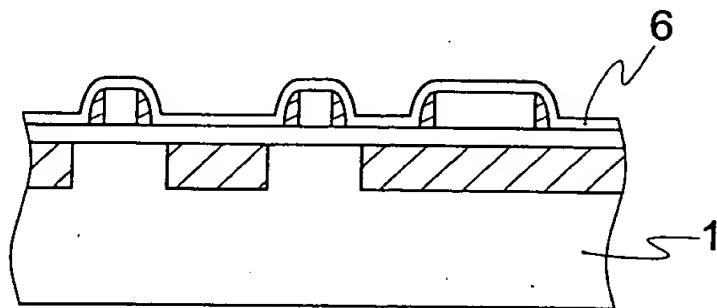


FIG. 15 (b)

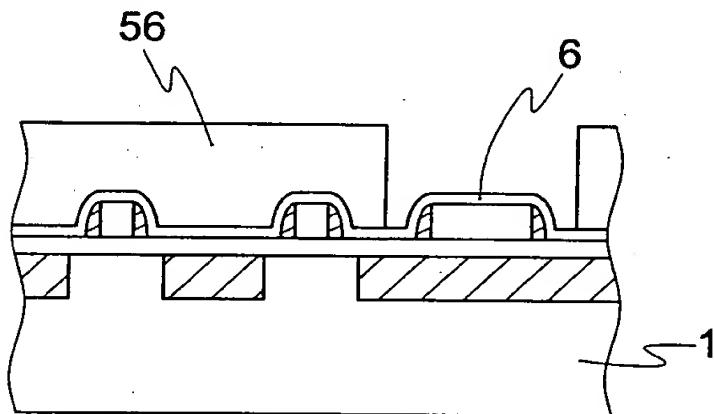
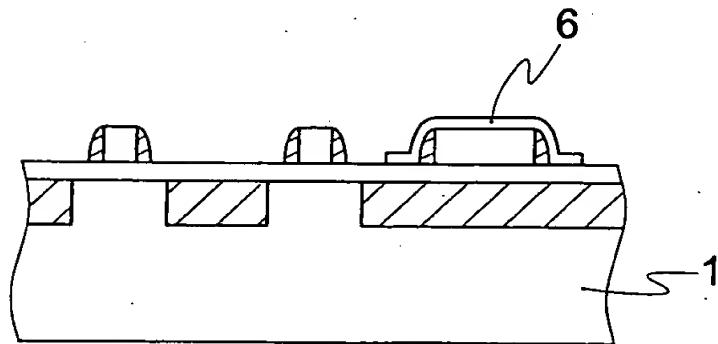


FIG. 15 (c)



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FIG. 16 (a)

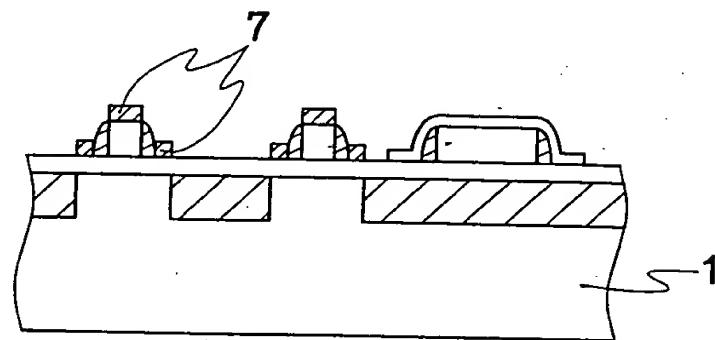
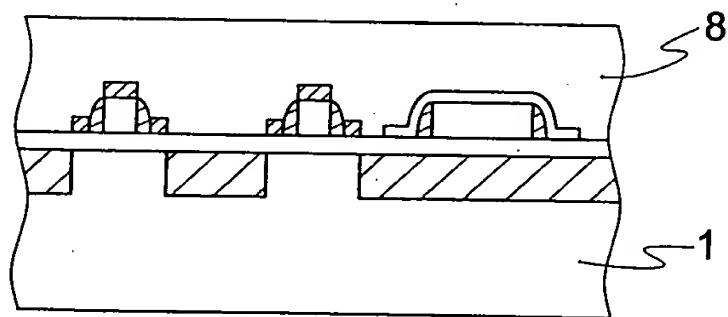


FIG. 16 (b)



Title: SI-MOS HIGH-FREQUENCY SEMICONDUCTOR DEVICE AND THE MANUFACTURING METHOD
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FIG. 17 (a)

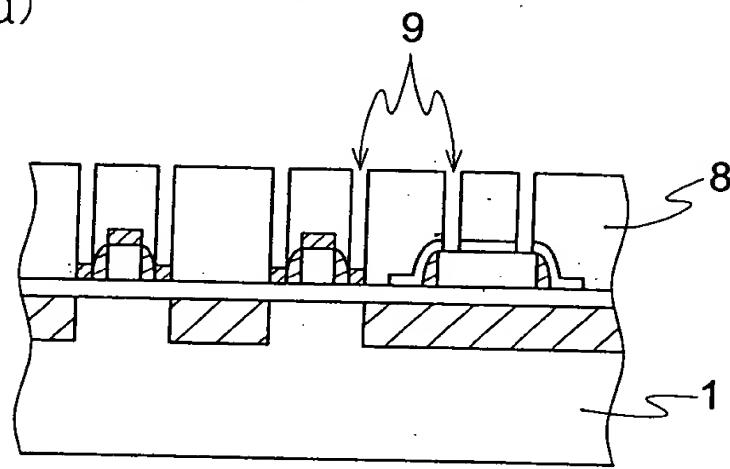
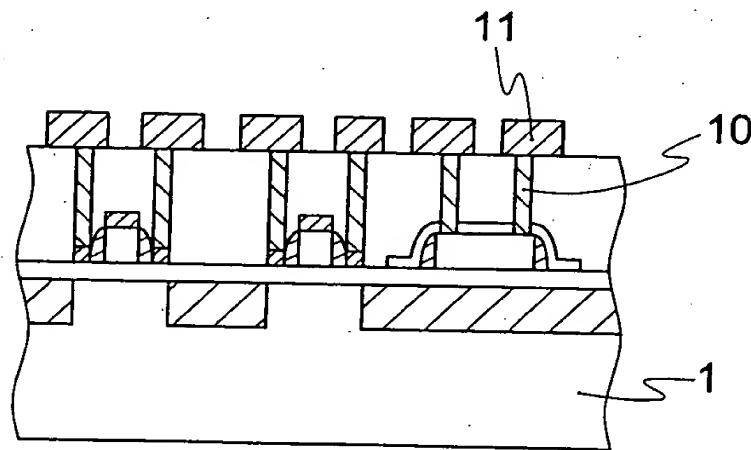


FIG. 17 (b)



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FIG. 18(a)

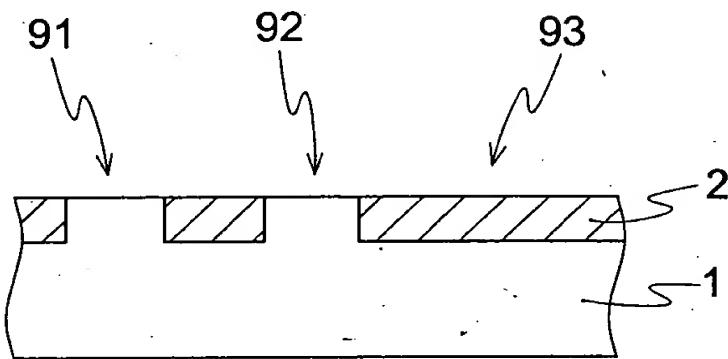


FIG. 18(b)

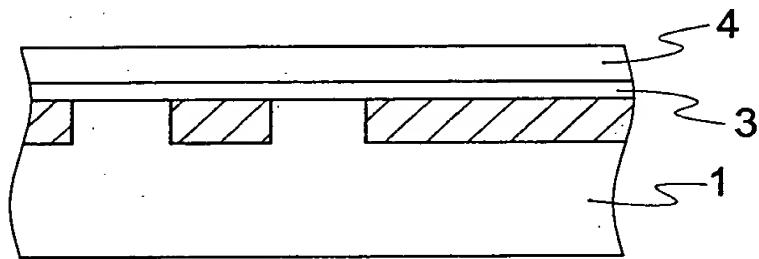
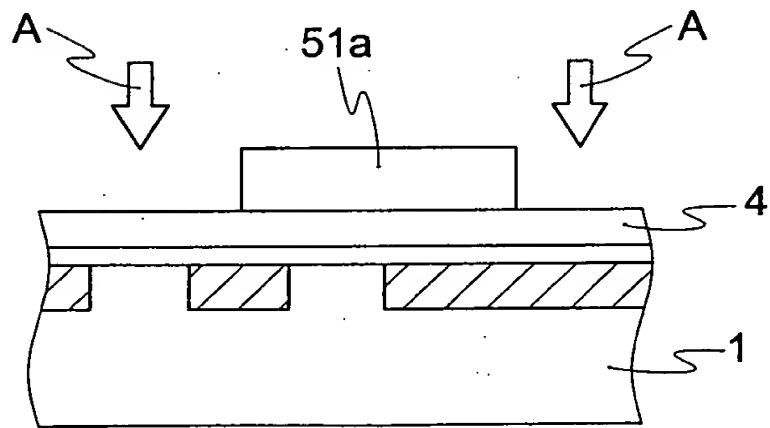


FIG. 18(c)



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FIG. 19(a)

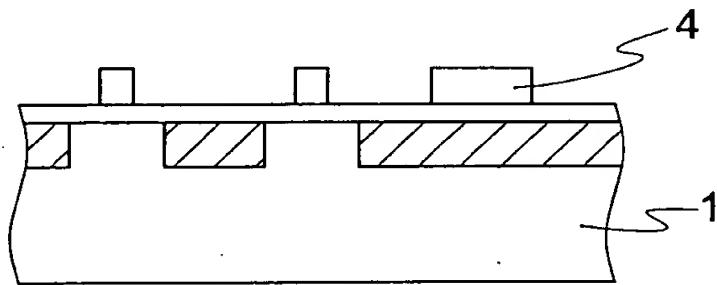


FIG. 19(b)

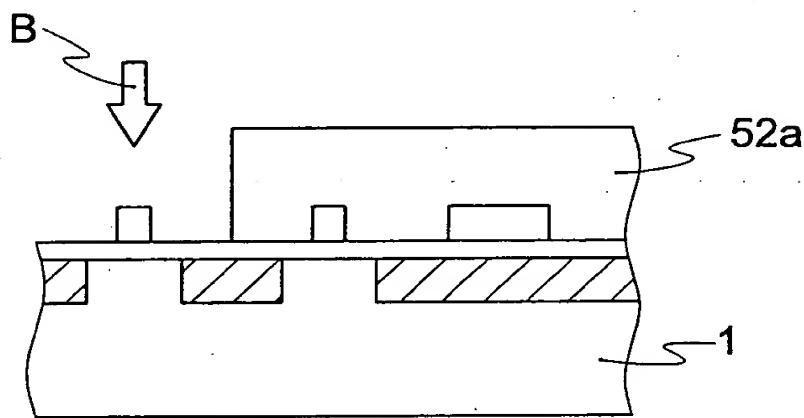
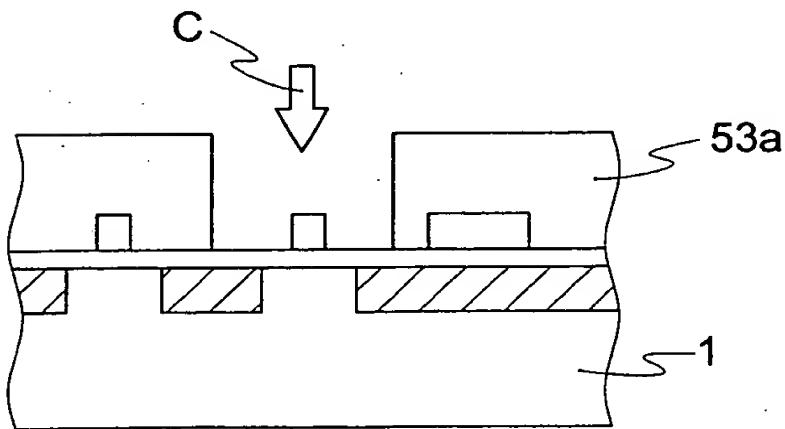


FIG. 19(c)



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FIG. 20(a)

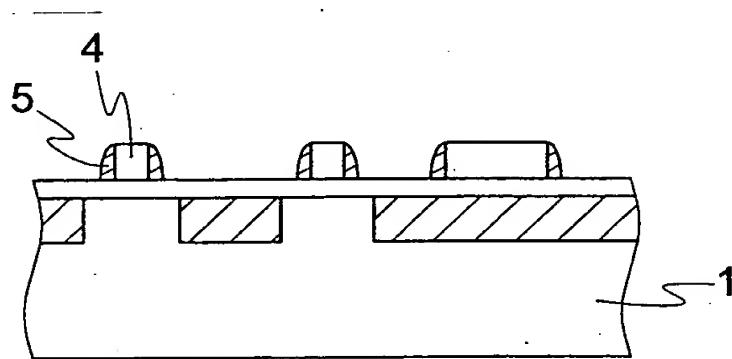


FIG. 20(b)

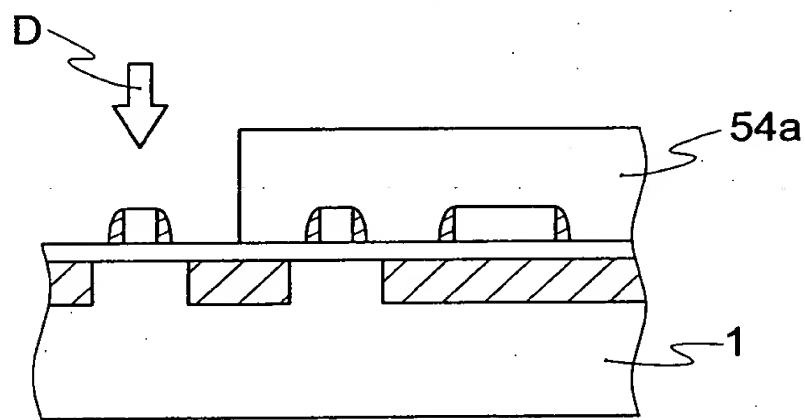
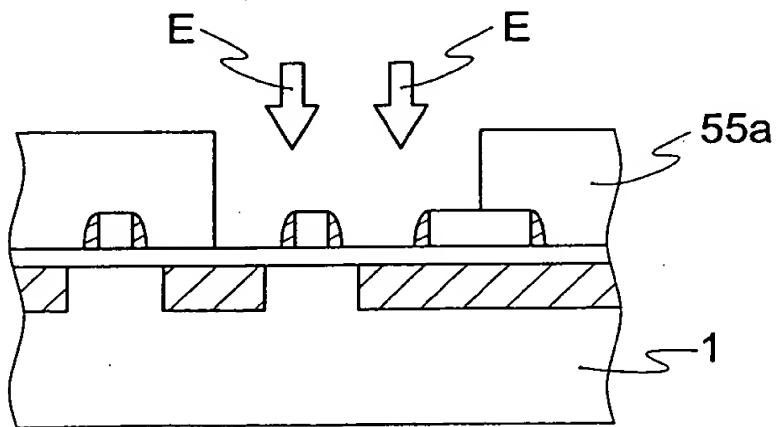


FIG. 20(c)



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FIG. 21(a)

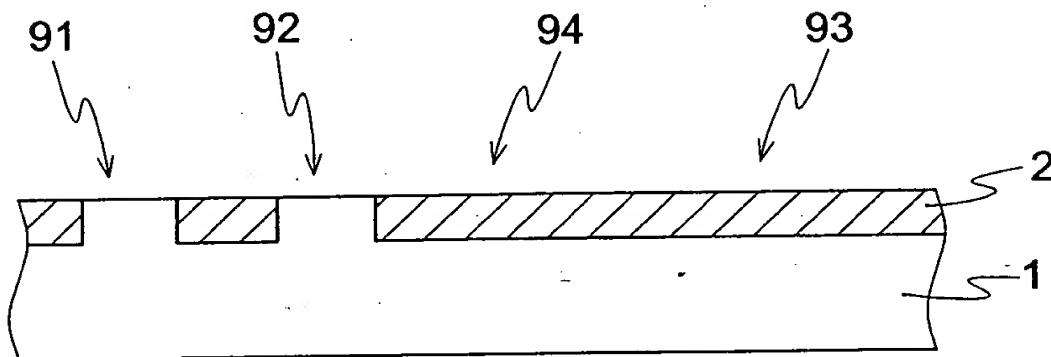


FIG. 21(b)

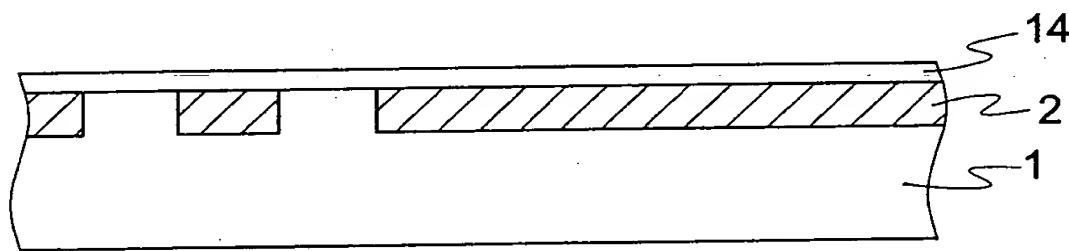
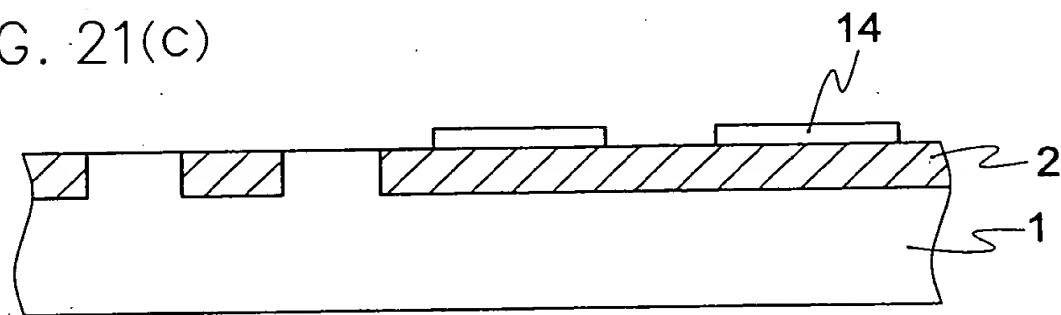


FIG. 21(c)



Title: SI-MOS HIGH-FREQUENCY SEMICONDUCTOR DEVICE AND THE MANUFACTURING METHOD
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FIG. 22(a)

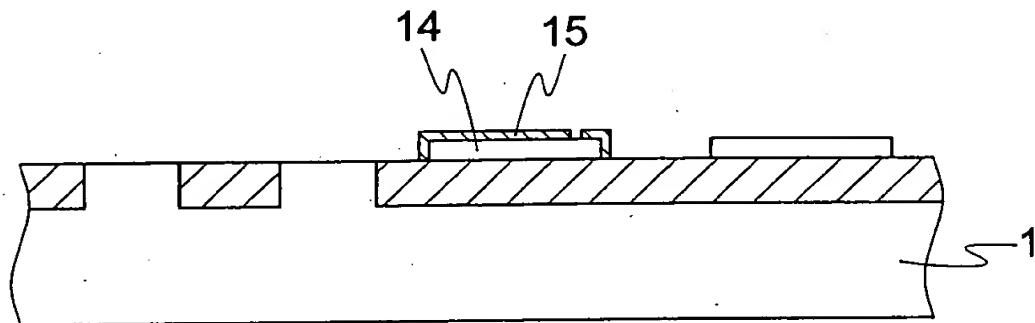


FIG. 22(b)

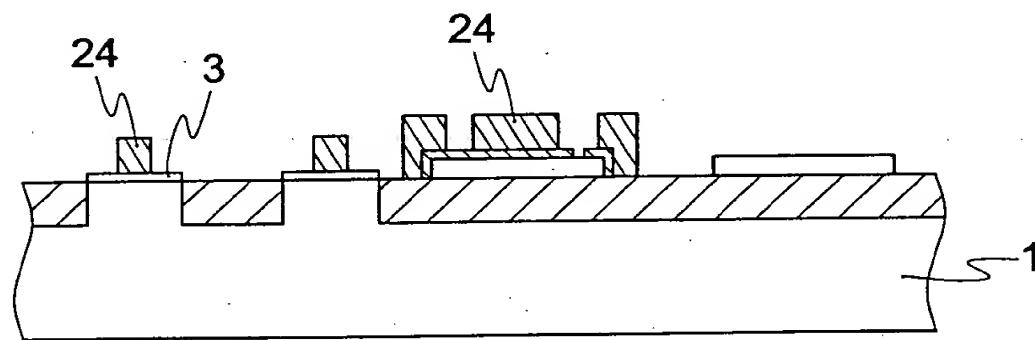
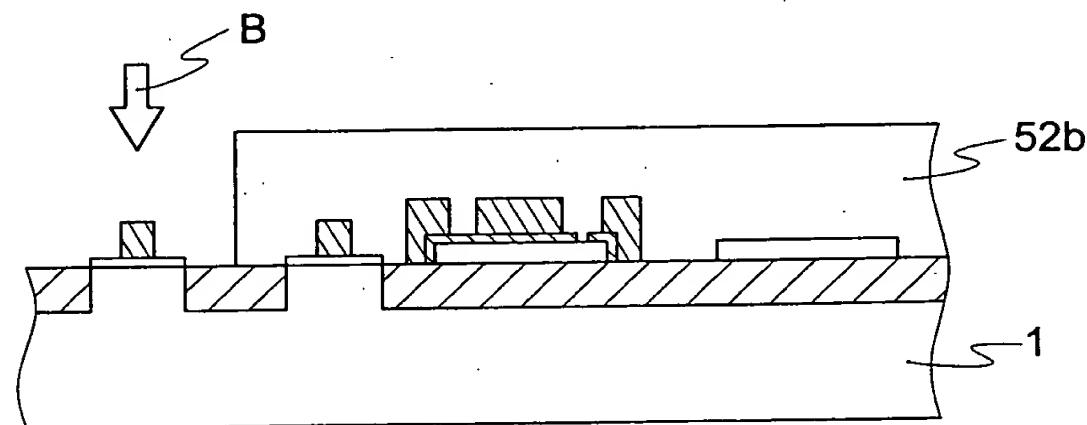


FIG. 22(c)



Title: SI-MOS HIGH-FREQUENCY SEMICONDUCTOR DEVICE AND THE MANUFACTURING METHOD
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FIG. 23(a)

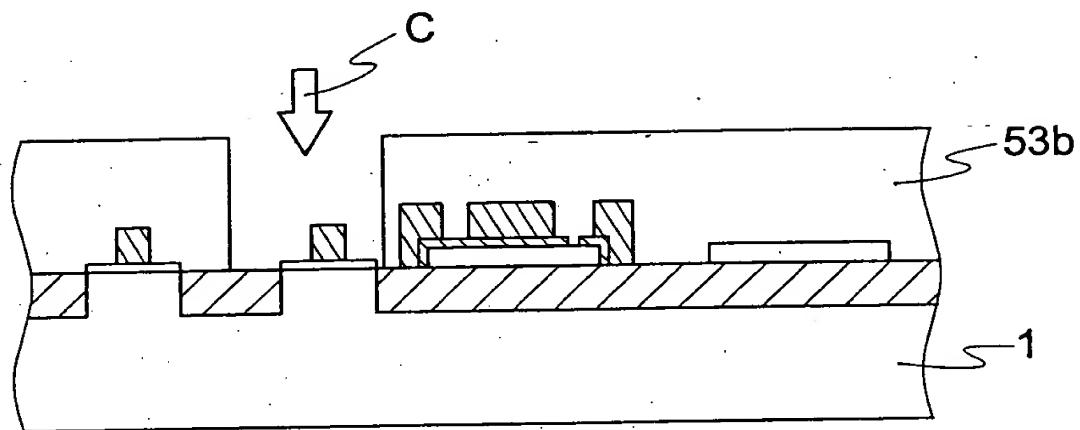
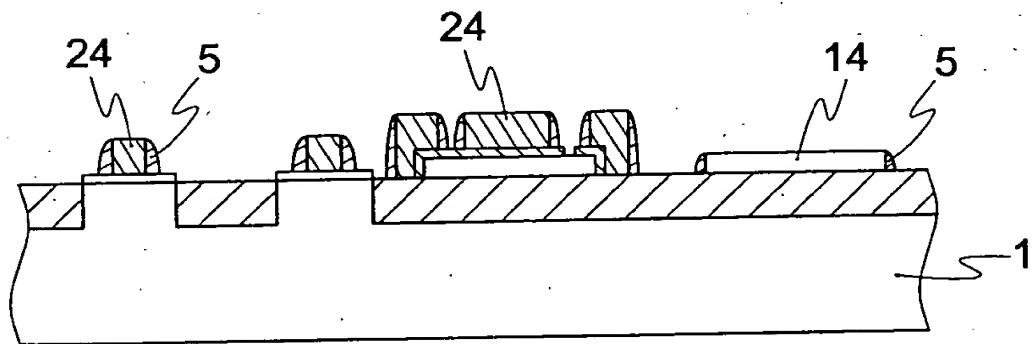


FIG. 23(b)



Title: SI-MOS HIGH-FREQUENCY SEMICONDUCTOR DEVICE AND THE MANUFACTURING METHOD
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FIG. 24(a)

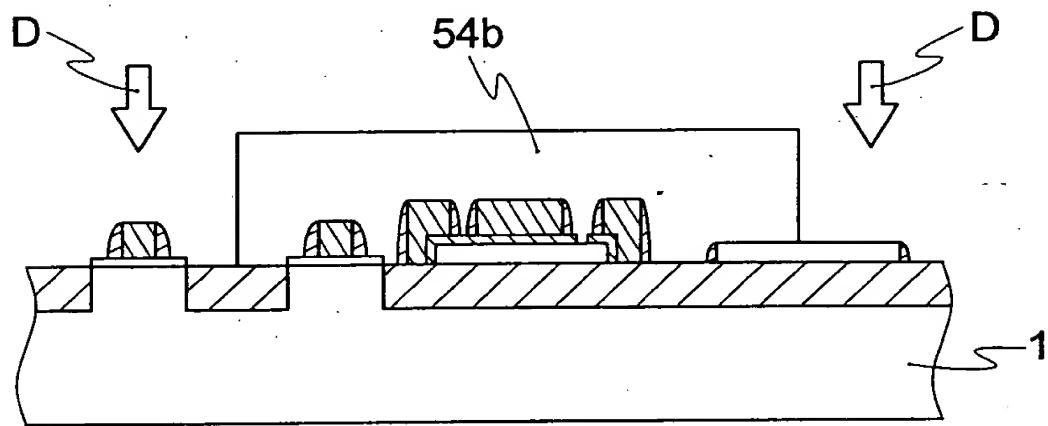


FIG. 24(b)

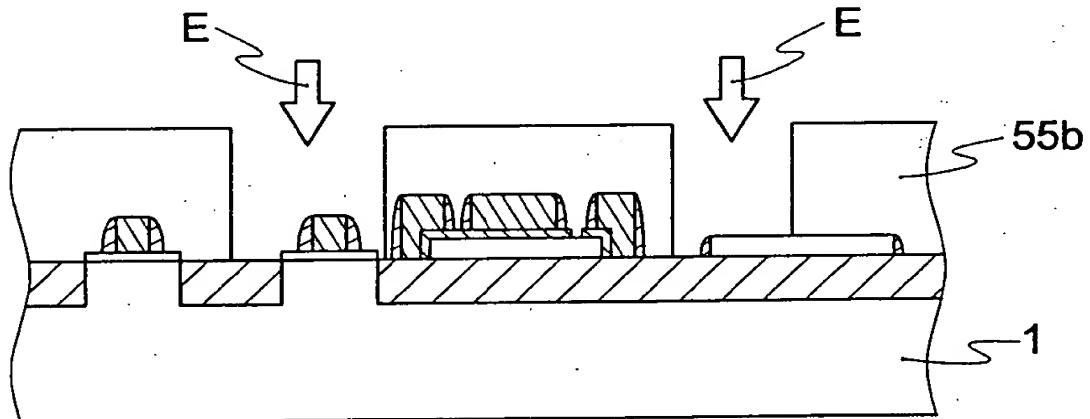


FIG. 25(a)

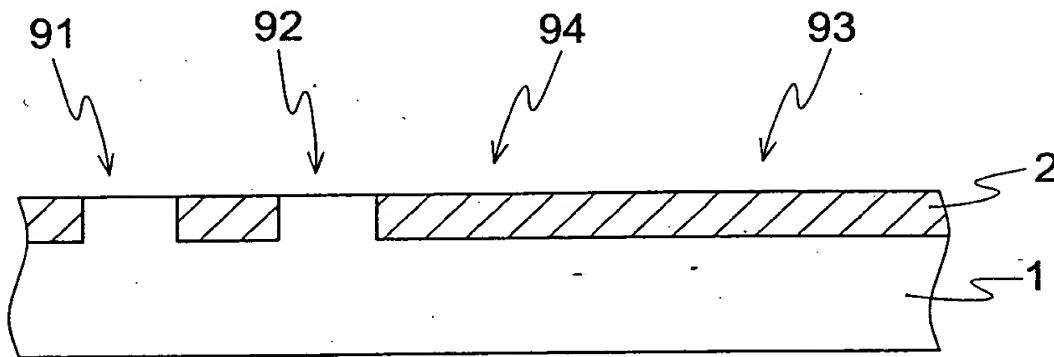


FIG. 25(b)

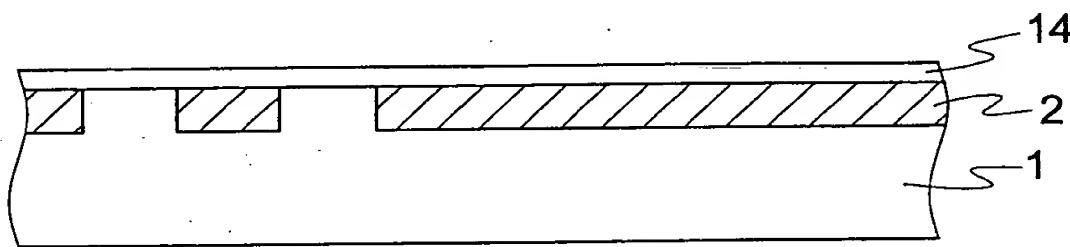
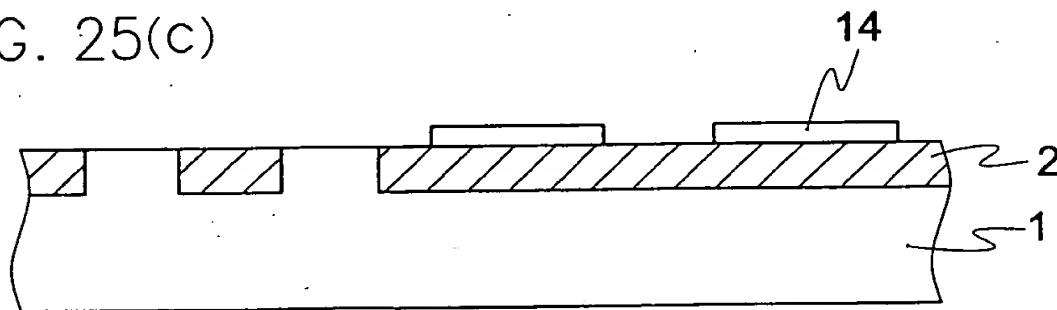


FIG. 25(c)



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FIG. 26(a)

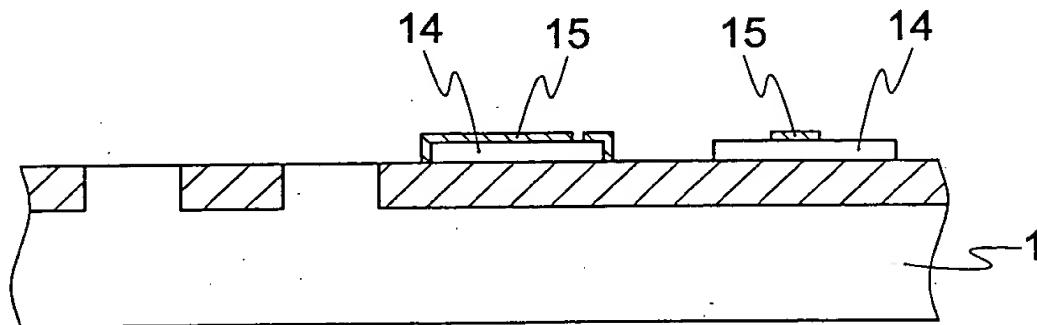


FIG. 26(b)

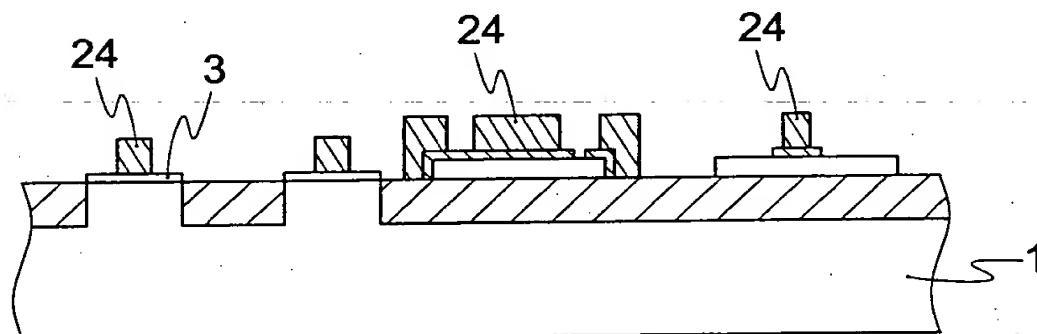
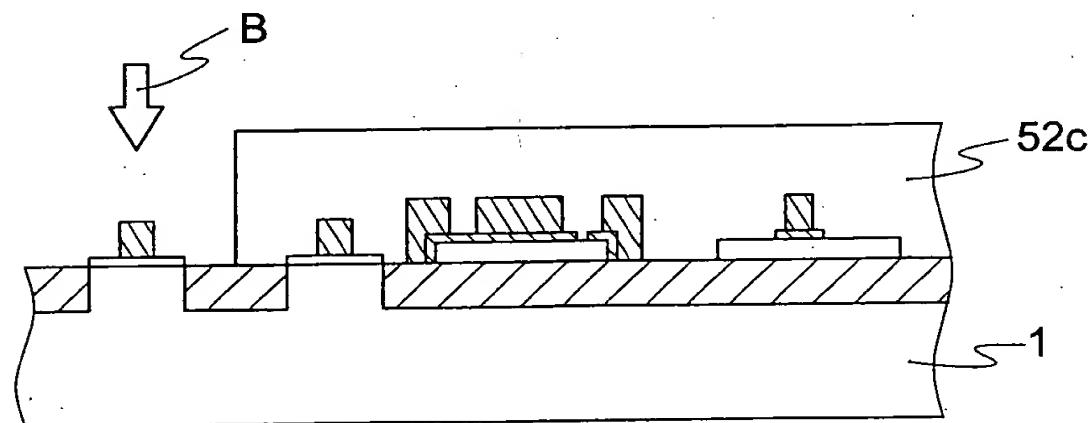


FIG. 26(c)



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FIG. 27 (a)

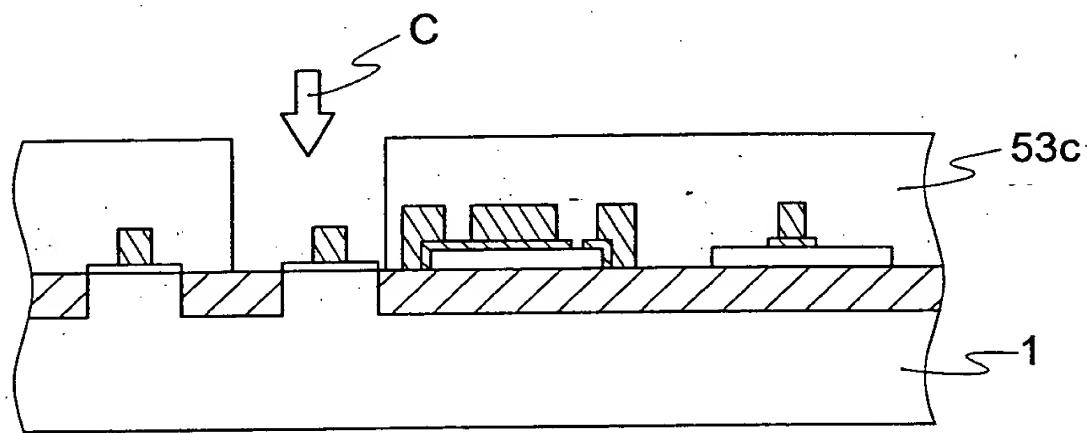
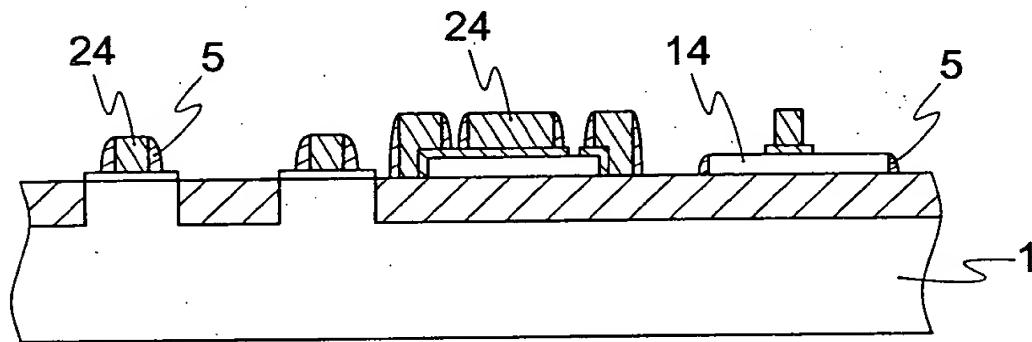


FIG. 27 (b)



Title: SI-MOS HIGH-FREQUENCY SEMICONDUCTOR DEVICE AND THE MANUFACTURING METHOD
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Inventors: Takahiro OHNAKADO
Atty Docket No.: 401308
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FIG. 28(a)

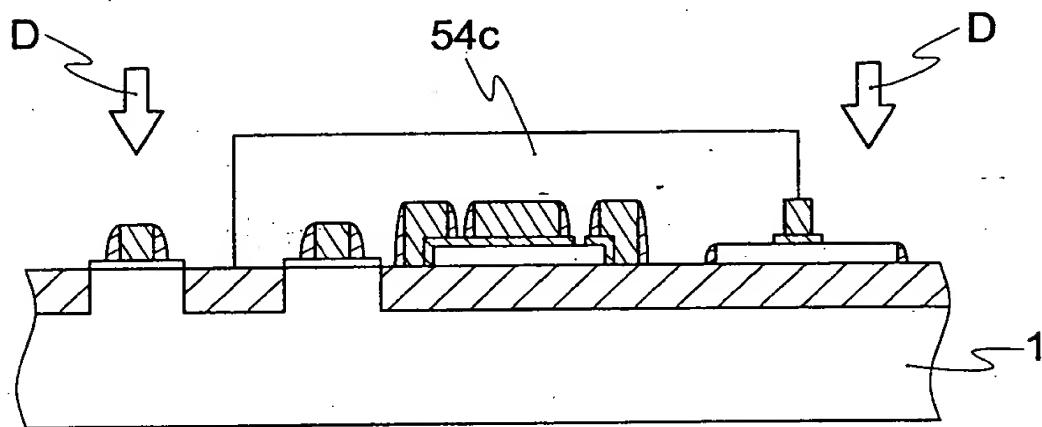
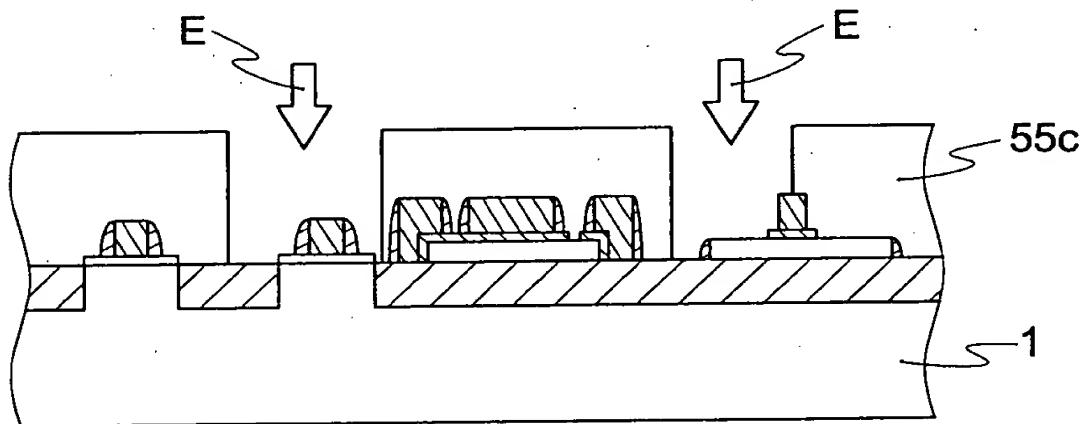


FIG. 28(b)



Title: SI-MOS HIGH-FREQUENCY SEMICONDUCTOR DEVICE AND THE MANUFACTURING METHOD
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Atty Docket No.: 401308
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FIG. 29(a)

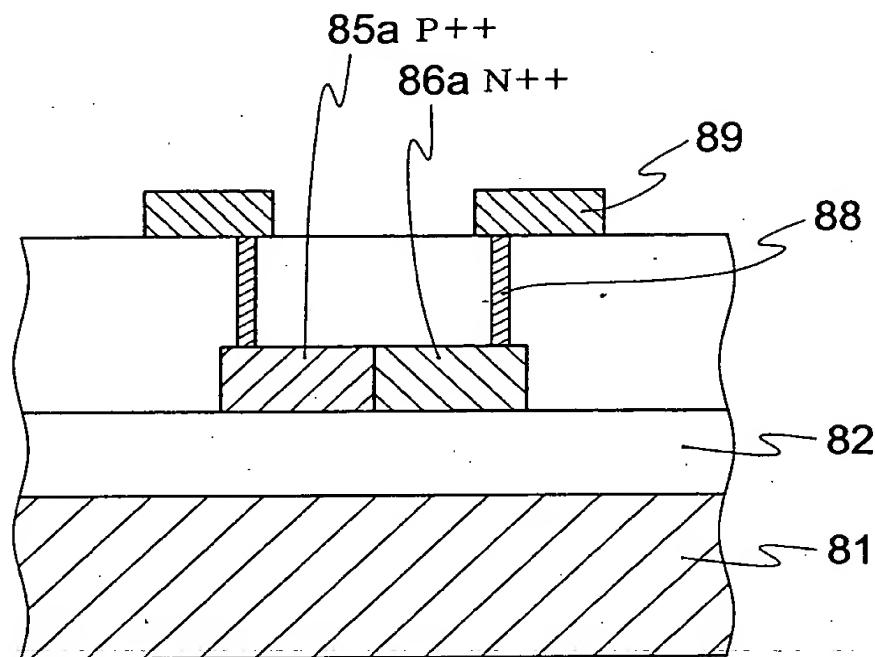
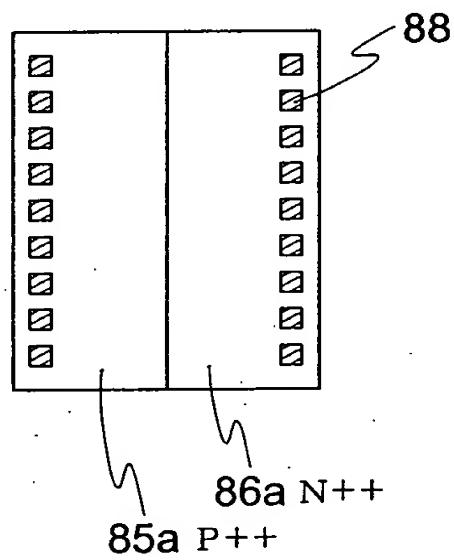


FIG. 29(b)



Title: SI-MOS HIGH-FREQUENCY SEMICONDUCTOR DEVICE AND THE MANUFACTURING METHOD
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Leydig, Voit & Mayer, Ltd.
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FIG. 30(a)

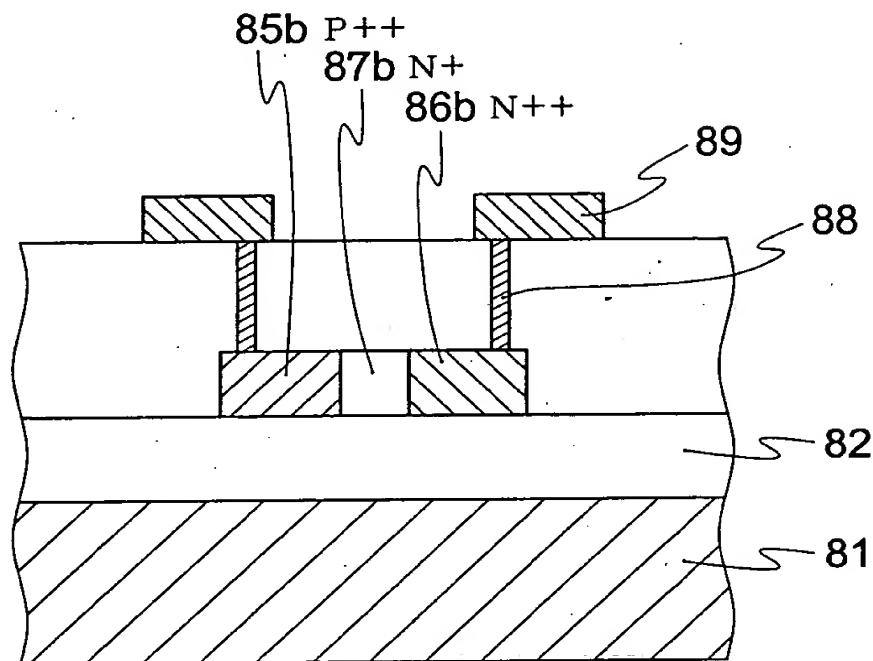
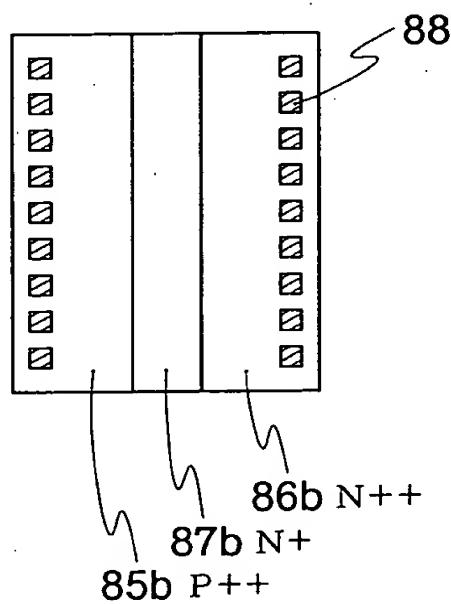


FIG. 30(b)



Title: SI-MOS HIGH-FREQUENCY SEMICONDUCTOR DEVICE AND THE MANUFACTURING METHOD
OF THE SAME
Inventors: Takahiro OHNAKADO
Atty Docket No.: 401308
Leydig, Voit & Mayer, Ltd.
202-737-6770

FIG. 31(a)

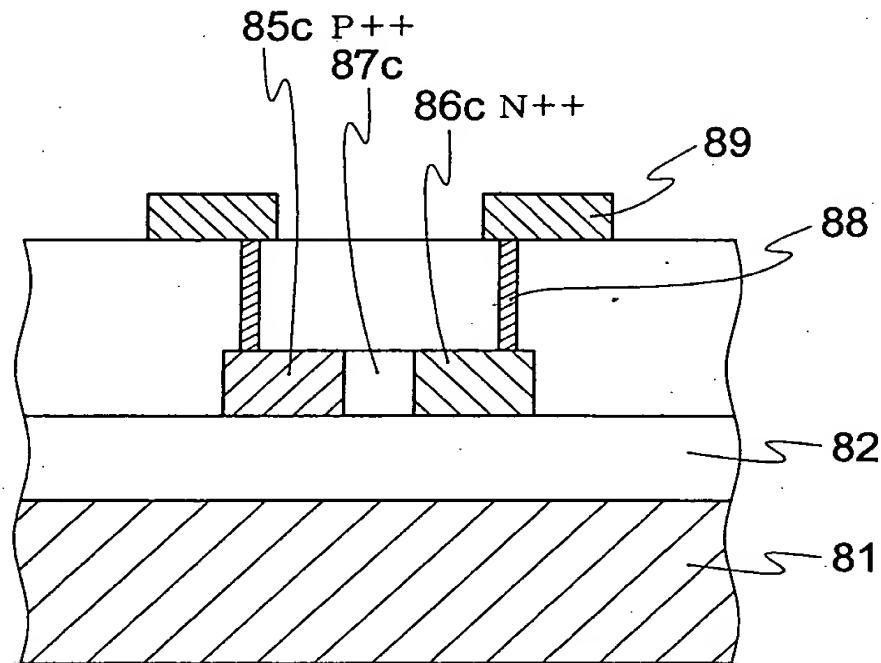
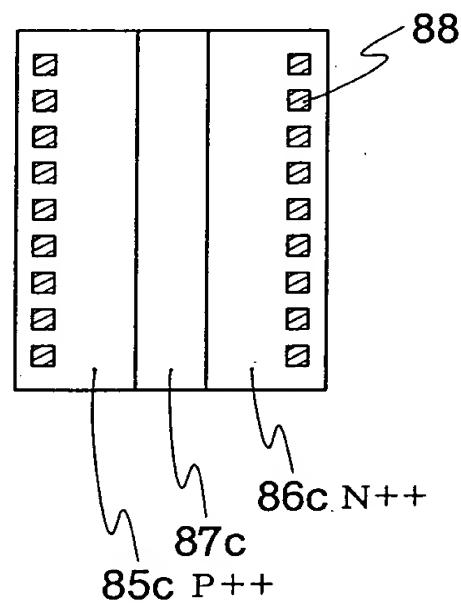


FIG. 31(b)



Title: SI-MOS HIGH-FREQUENCY SEMICONDUCTOR DEVICE AND THE MANUFACTURING METHOD
OF THE SAME
Inventors: Takahiro OHNAKADO
Atty Docket No.: 401308
Leydig, Voit & Mayer, Ltd.
202-737-6770

FIG. 32(a)

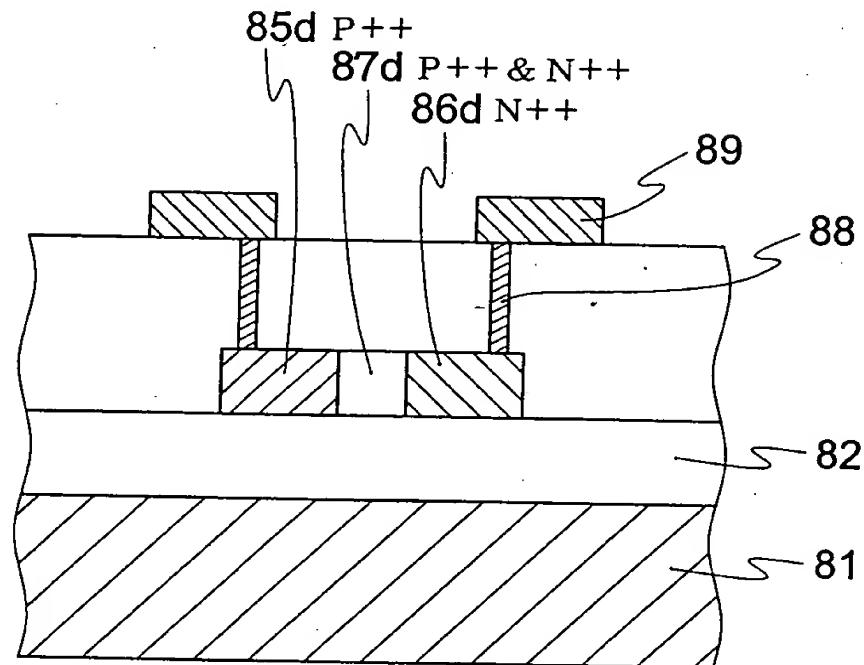
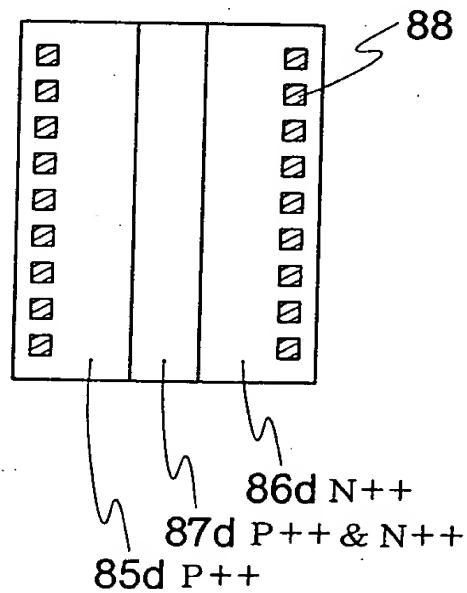
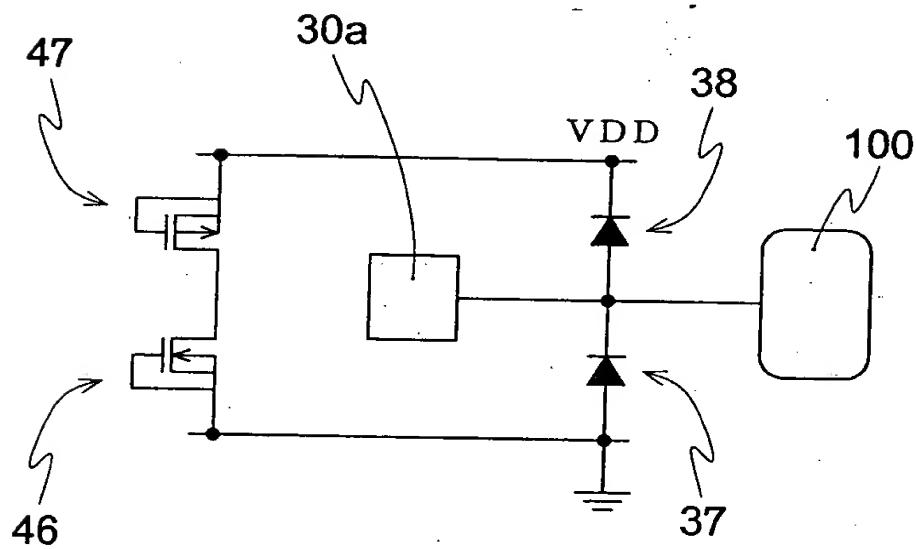


FIG. 32(b)



Title: SI-MOS HIGH-FREQUENCY SEMICONDUCTOR DEVICE AND THE MANUFACTURING METHOD
OF THE SAME
Inventors: Takahiro OHNAKADO
Atty Docket No.: 401308
Leydig, Voit & Mayer, Ltd.
202-737-6770

FIG. 33



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FIG. 34(a)

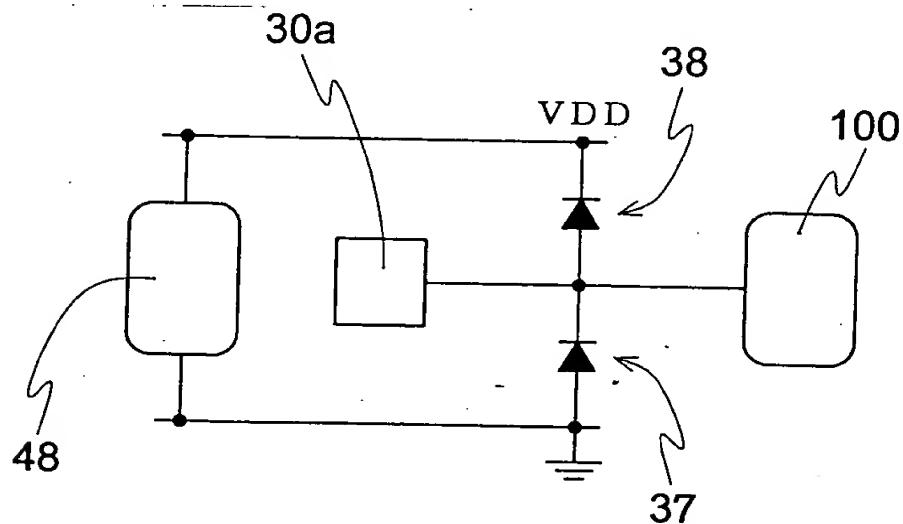


FIG. 34(b)

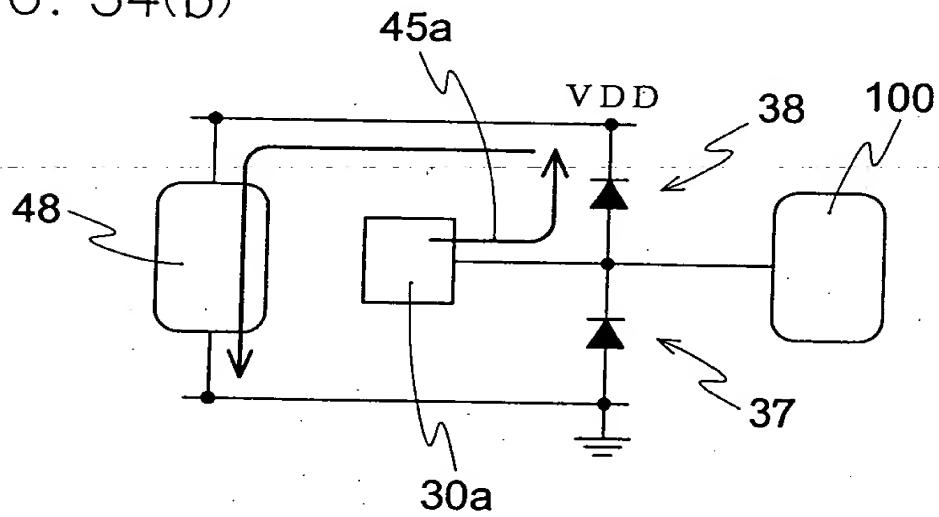


FIG. 34(c)

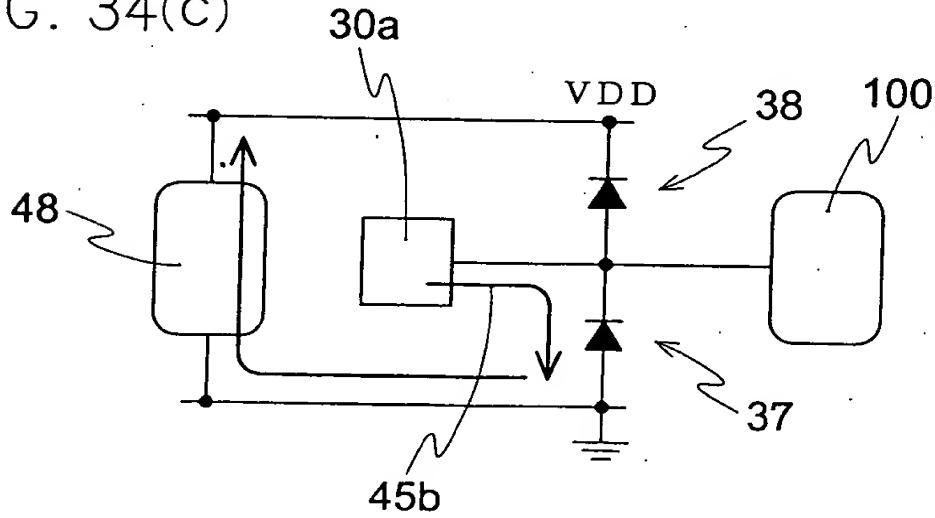
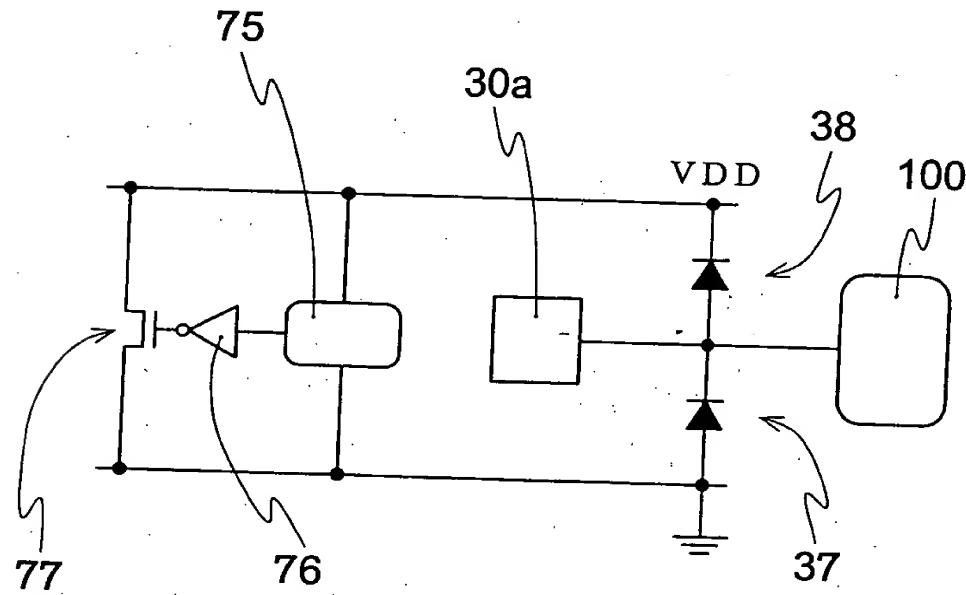


FIG. 35



4052207 TESTED

FIG. 36

